

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please CANCEL claims 4 and 6-17, and AMEND claim 1 in accordance with the following:

1. (Currently Amended) A thin film forming method for plasmatizing a mixture gas, the mixture gas consisting of a monomer gas and an oxidizing reactive gas, and for forming a thin film on a surface of a substrate, the thin film being made of an oxide, comprising:
a first step of forming a first thin film by plasmatizing the mixture gas while varying a flow amount ratio of the monomer gas with respect to the reactive gas; and
a second step of forming a final thin film by increasing the flow amount ratio after the first film forming step, wherein:
the first step of forming the first thin film is performed under the a first condition that the flow amount ratio is 0.05 or lower within 2 to 5 seconds[[:]], and the flow amount of monomer gas is gradually reduced while the amount of the oxidizing reactive gas is maintained at a substantially fixed level; and
the second step of forming the final thin film is performed under a second condition that the flow amount ratio of monomer gas with respect to the reactive gas reaches 1000 or more, and the second step of forming the final thin film lasts for 1 to 3 seconds.
2. (Original) A thin film forming method according to claim 1, wherein the flow amount ratio decreases continuously in the first thin film forming step.
3. (Original) A thin film forming method according to claim 2, wherein an initial value of the flow amount ratio in the first thin film forming step is in a range of 0.02 to 0.2.
4. (Cancelled).
5. (Original) A thin film forming method according to claim 1, 2 or 3, wherein the

mixture gas is plasmatized by controlling reflected power to be 10% or lower than supplied high frequency power, the reflected power being generated by supplying high frequency power of 100 MHz or lower to a high frequency electrode through an impedance matching network.

6-17. (Cancelled).